

NTT-AT provides GaN epitaxial wafers with high mobility for electronic devices

GaN EPITAXIAL WAFERS

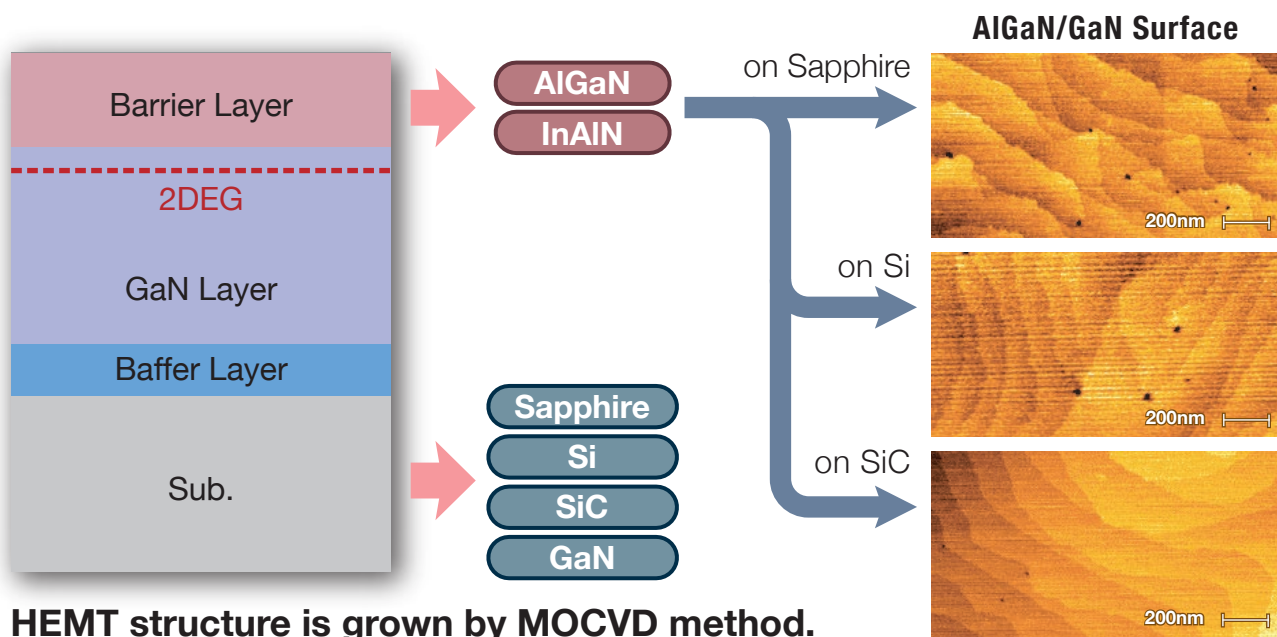


- GaN epitaxial wafers using various substrates (Sapphire, Si, SiC, GaN)
- Able to provide large size substrate (up-to 8 inch with Si substrate)
- Widely accepted by the electronic device market
- Novel fabrication technique based on the cutting-edge technologies of NTT Laboratories

GaN HEMT Epi Products

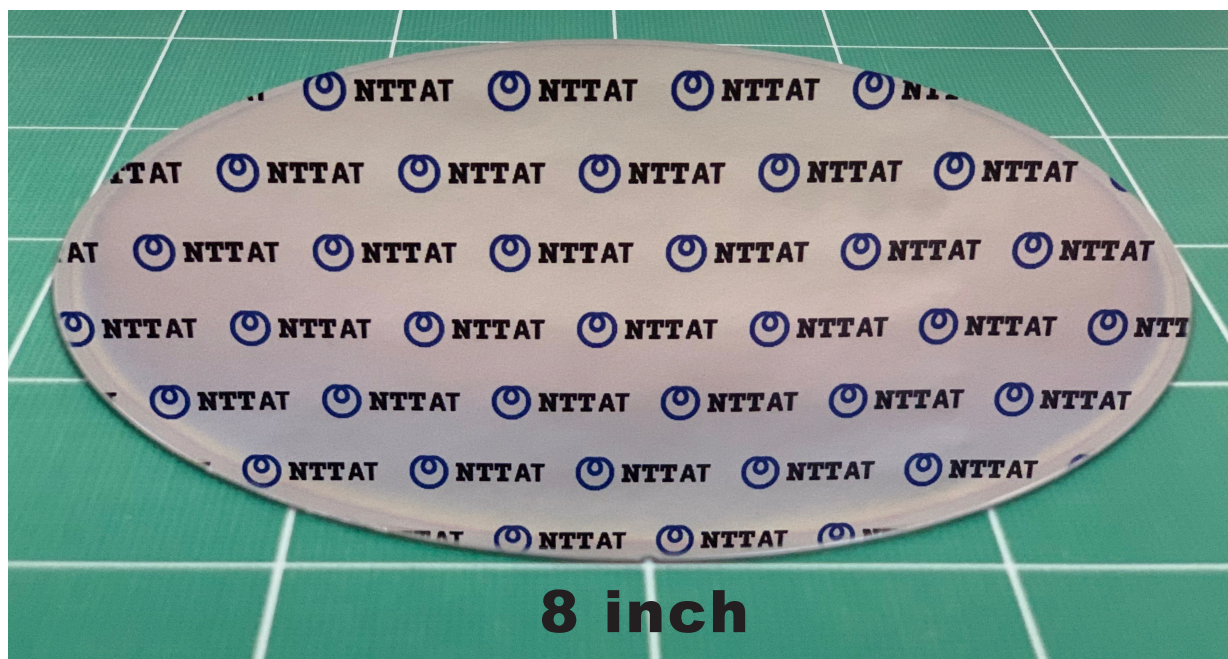
Epi	Size	Substrate
AlGaIn/GaN HEMT Epi InAlN/GaN HEMT Epi	2~3 inch	Sapphire
	4~8 inch	Si
	4~6 inch	SiC
	2~4 inch	GaN

Layer Structure and AFM Images of HEMT epi surface



Now, 8 inch GaN on Si available

GaN Epitaxial Wafers



Standard fabrication process

1. Formulate crystal growth conditions
2. Substrate cleaning
3. Epitaxial growth
4. Non destructive inspection of crystal quality by X-ray diffraction

Other optional inspection services are available to meet your needs

- Thickness uniformity
- Composition uniformity
- Sheet resistance
- Mobility
- AFM
- Surface particle inspection

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- ▶ **NTT-AT is pleased to “customize” our GaN epi-wafer according to your needs.**
 - ▶ **Please let us know your required layer structure and quantity.**
For any further questions, please feel free to contact us.
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Notes:

This content may be subject to change without notice.

This product has been classified under Item 7(18) in the Export Control Order Attachment List 1 by Japan's Ministry of Economy, Trade and Industry (METI), and a license from METI is required for its export.

For more information, please contact

NTT Advanced Technology Corporation

URL https://keytech.ntt-at.co.jp/en/epi/prd_1002.html